

AMENDMENT TO THE SPECIFICATION

Please replace the paragraph on page 11, lines 12-17 with the following amended paragraph:

As further shown in FIG. 2(j), the oxide above the gate polysilicon of the NFETs is etched off while the vertical oxide bird's beak is still preserved. The stresses created in the gate polysilicon of the NFETs are maintained even after removal of this oxide on top of the polysilicon as a result of the vertical bird's beak formed in the gate polysilicon of the NFETs because of the oxidation step, as shown in Figures 4 and 5. As also shown in FIG. 20), the mask 38 has been removed.